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SEMICONDUCTOR



ESD



TVS



TSS



MOV

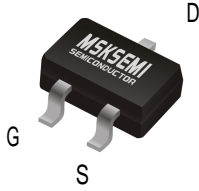


GDT

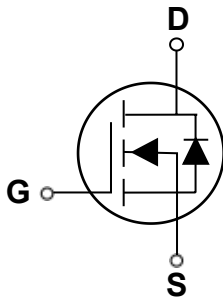


PLED

Product data sheet



SOT-23-3L



Features

- 30V, 4.0 A, $R_{DS(ON)} = 47m\Omega @ V_{GS} = 4.5V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Notebook
- Load Switch
- LED applications

BVDSS	RDSON	ID
30V	47mΩ	4.0A

Absolute Maximum Ratings $T_c=25$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±12	V
I_D	Drain Current – Continuous ($T_c=25^\circ C$)	4.0	A
	Drain Current – Continuous ($T_c=100^\circ C$)	3.0	A
I_{DM}	Drain Current – Pulsed ¹	16	A
P_D	Power Dissipation ($T_c=25^\circ C$)	1.4	W
	Power Dissipation – Derate above 25°C	0.012	W/°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	80	°C/W

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.06	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =125°C	---	---	10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±12V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V, I _D =4A	---	47	60	mΩ
		V _{GS} =2.5V, I _D =3A	---	60	85	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.5	0.9	1.4	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-3	---	mV/°C
g _{fs}	Forward Transconductance	V _{DS} =10V, I _S =3A	---	7	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{2,3}	V _{DS} =10V, V _{GS} =4.5V, I _D =3A	---	8.4	---	nC
Q _{gs}	Gate-Source Charge ^{2,3}		---	1	---	
Q _{gd}	Gate-Drain Charge ^{2,3}		---	2.2	---	
T _{d(on)}	Turn-On Delay Time ^{2,3}	V _{DD} =10V, V _{GS} =4.5V, R _G =25Ω I _D =1A	---	4.5	---	nS
T _r	Rise Time ^{2,3}		---	13	---	
T _{d(off)}	Turn-Off Delay Time ^{2,3}		---	27	---	
T _f	Fall Time ^{2,3}		---	8.3	---	
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, F=1MHz	---	695	---	pF
C _{oss}	Output Capacitance		---	45	---	
C _{rss}	Reverse Transfer Capacitance		---	36	---	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	1.5	---	Ω

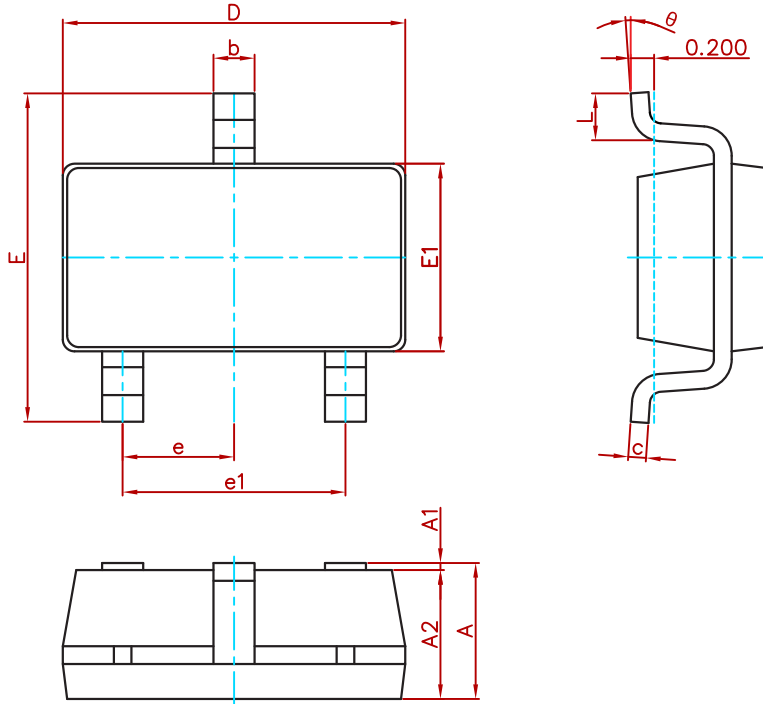
Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	4.0	A
I _{SM}	Pulsed Source Current		---	---	8.0	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

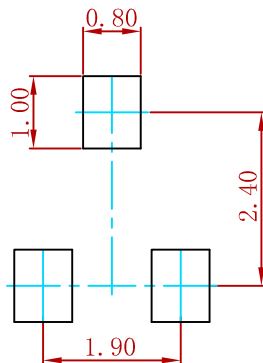
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
AO3402	SOT-23-3L	3000

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